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Team Nexperia



PMV16UN

20 V, 5.8 A N-channel Trench MOSFET Rev. 1 — 4 April 2011

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

Low threshold voltage

Trench MOSFET technology

Very fast switching

1.3 Applications

Relay driver

■ High-speed line driver

Low-side loadswitch

Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	5.8	Α
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5.8 \text{ A};$ $T_j = 25 \text{ °C}$		-	15	18	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	_ 3	D
3	D	drain	1 2	G_(I
			SOT23 (TO-236AB)	mbb076 \$

3. Ordering information

Table 3. Ordering information

Type number	umber Package					
	Name	Description	Version			
PMV16UN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV16UN	KV%

^{[1] % =} placeholder for manufacturing site code

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		3 - 7 (
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	5.8	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	<u>[1]</u>	-	3.6	Α
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$		-	25	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			<u>[1]</u>	-	930	mW
		T _{sp} = 25 °C		-	4170	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

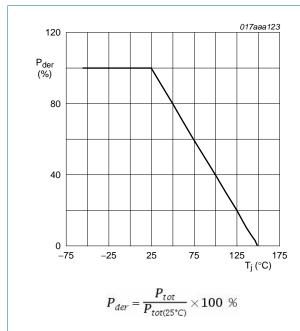


Fig 1. Normalized total power dissipation as a function of junction temperature

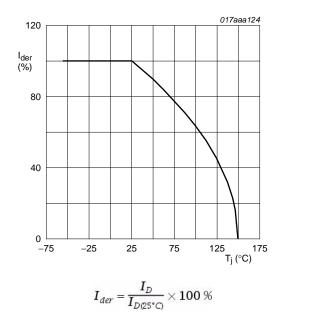
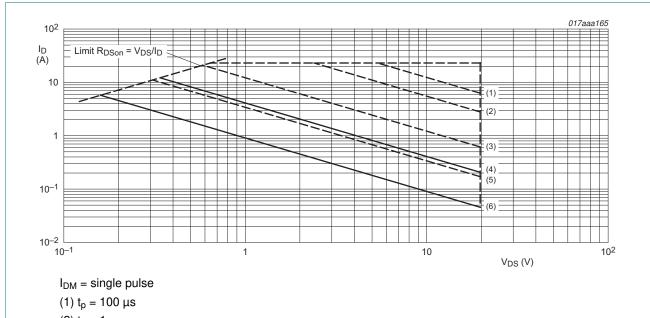


Fig 2. Normalized continuous drain current as a function of junction temperature

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(2) $t_p = 1 \text{ ms}$

(3) $t_p = 10 \text{ ms}$

(4) DC; $T_{sp} = 25 \, ^{\circ}C$

 $(5) t_p = 100 \text{ ms}$

(6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

20 V, 5.8 A N-channel Trench MOSFET

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	207	245	K/W
			<u>[2]</u>	-	116	135	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

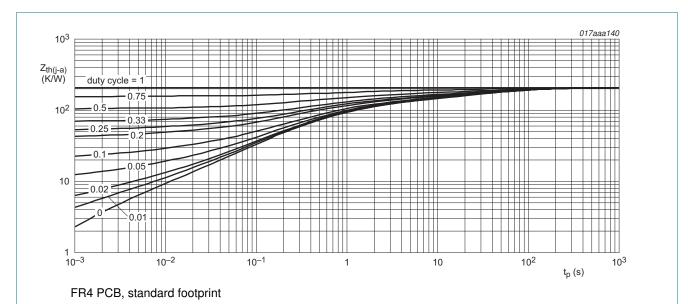


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

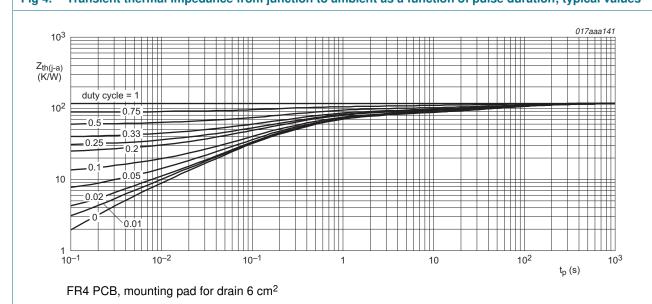


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.7	1	V
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	20	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 5.8 \text{ A}; T_j = 25 \text{ °C}$	-	15	18	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5.8 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	23	28	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 5.1 \text{ A}; T_j = 25 \text{ °C}$	-	18	23	mΩ
		$V_{GS} = 1.8 \text{ V}; I_D = 3.9 \text{ A}; T_j = 25 \text{ °C}$	-	25	40	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	18	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 3 A$; $V_{DS} = 10 V$; $V_{GS} = 4.5 V$;	-	7.4	11	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1	-	nC
Q_{GD}	gate-drain charge		-	1.9	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V}; f = 1 \text{ MHz};$	-	670	-	рF
C _{oss}	output capacitance	T _j = 25 °C	-	195	-	рF
C_{rss}	reverse transfer capacitance		-	85	-	pF
t _{d(on)}	turn-on delay time	$V_{DS}=10~V; V_{GS}=4.5~V; R_{G(ext)}=10~\Omega;$	-	12	-	ns
t _r	rise time	$T_j = 25 ^{\circ}\text{C}; I_D = 5.8 \text{A}$	-	40	-	ns
t _{d(off)}	turn-off delay time		-	170	-	ns
t _f	fall time		-	85	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	٧

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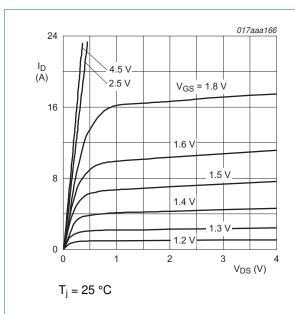
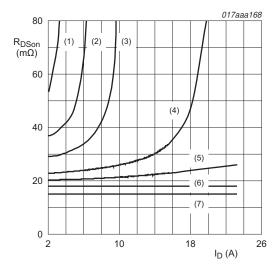


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_i = 25 °C

(1) $V_{GS} = 1.4 \text{ V}$

(2) $V_{GS} = 1.5 \text{ V}$

(3) $V_{GS} = 1.6 \text{ V}$

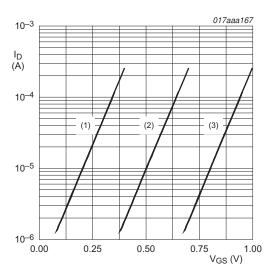
 $(4) V_{GS} = 1.8 V$

(5) $V_{GS} = 2.0 \text{ V}$

(6) $V_{GS} = 2.5 \text{ V}$

 $(7) V_{GS} = 4.5 V$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



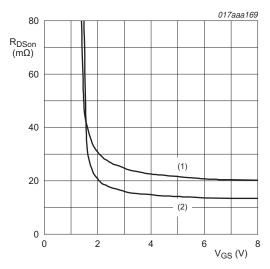
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 5.7 A$

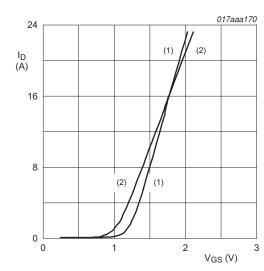
(1) $T_i = 150 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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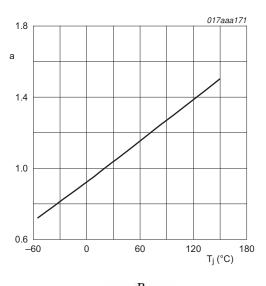


 $V_{DS} > I_{D} \times R_{DSon}$

(1)
$$T_i = 25 \, ^{\circ}C$$

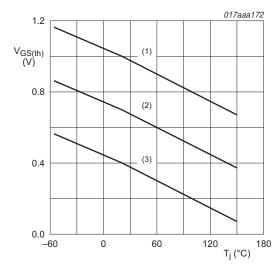
(2) $T_i = 150 \, ^{\circ}\text{C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$

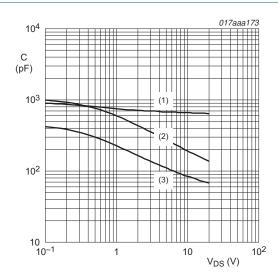
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

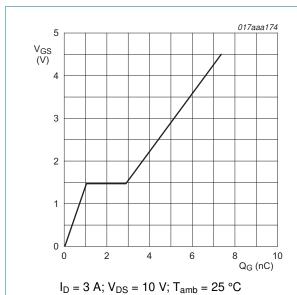


 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

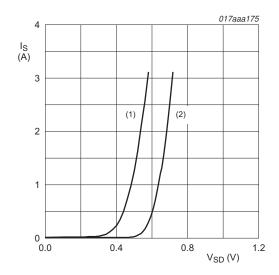
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V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_G(tot)
017aaa137

Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

(1) $T_j = 150 \, ^{\circ}C$

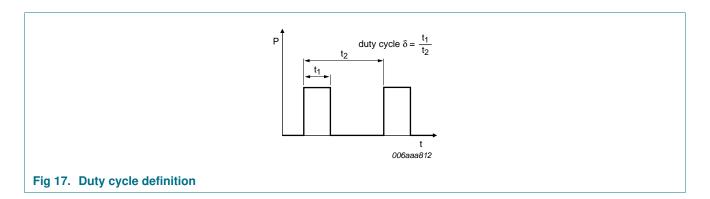
(2) $T_j = 25 \, {}^{\circ}\text{C}$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



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Package outline

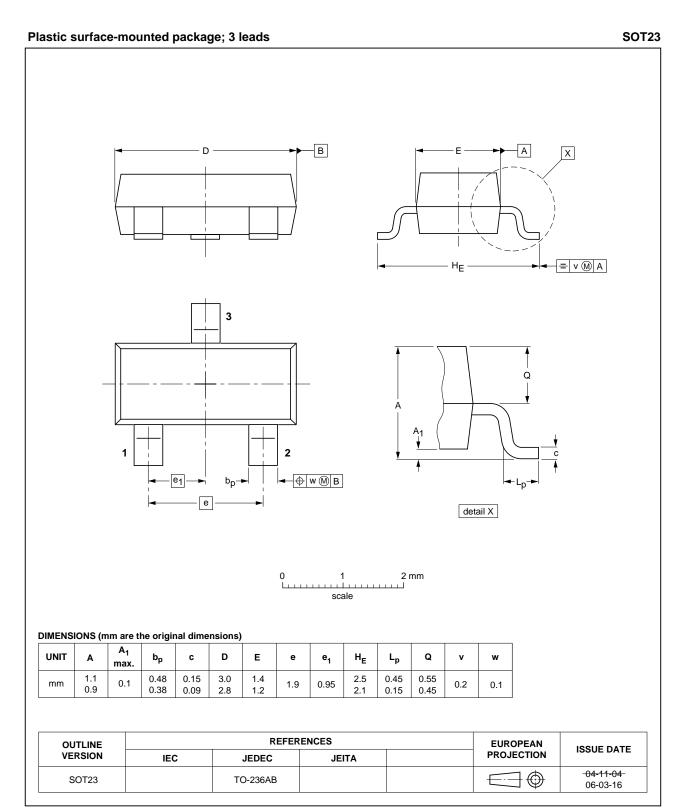


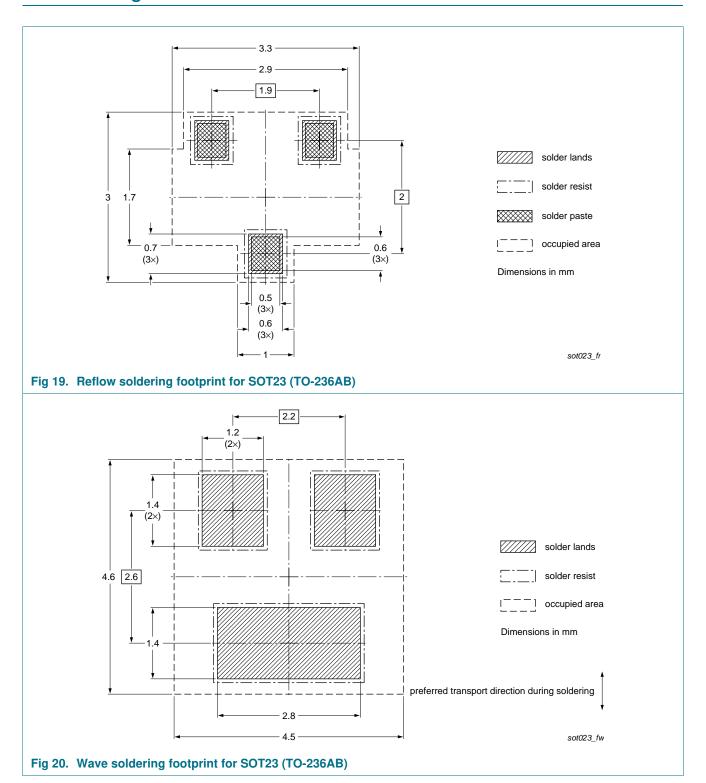
Fig 18. Package outline SOT23 (TO-236AB)

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10. Soldering



20 V, 5.8 A N-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMV16UN v.1	20110404	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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